HITACHI

2SC5141

Silicon NPN Epitaxial Transistor

Application

VHF & UHF wide band amplifier

Features

- High gain bandwidth product
  f_T = 5.8 GHz typ.
- High gain, low noise figure
  PG = 13 dB typ.,
  NF = 1.6 dB typ. at f = 900 MHz

SMPAK

1. Emitter
2. Base
3. Collector

Table 1 Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	20	V
Collector to emitter voltage	V_{CEO}	12	V
Emitter to base voltage	V_{EBO}	2	V
Collector current	I_C	50	mA
Collector power dissipation	P_C	80	mW
Junction temperature	T_j	150	°C
Storage temperature	Tstg	–55 to +150	°C

Note: Marking is "YN–"

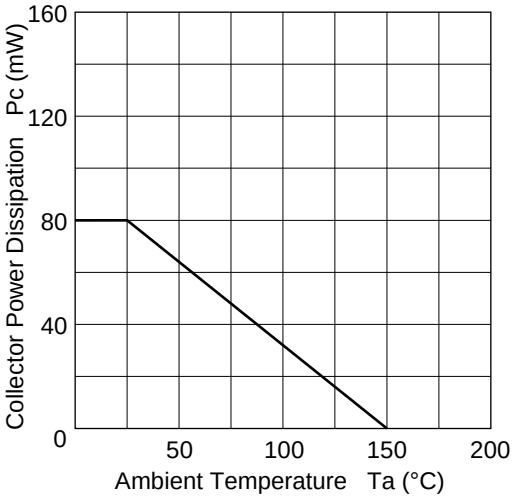
Attention: This device is very sensitive to electro static discharge.
It is recommended to adopt appropriate cautions when handling this transistor.

2SC5141

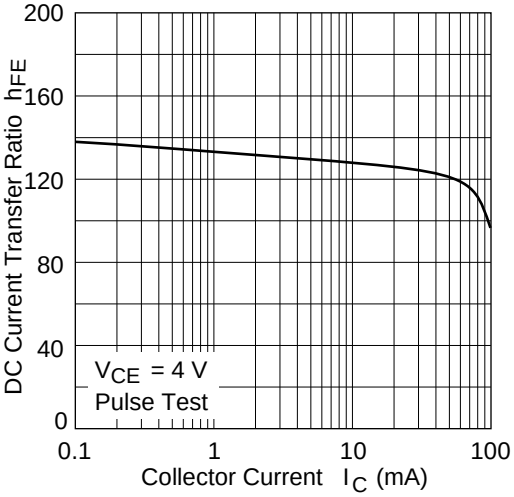
Table 2 Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min.	Typ.	Max.	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	20	—	—	V	I_C = 10 µA I_E = 0
Collector cutoff current	I_{CBO}	—	—	1	µA	V_{CB} = 15 V, I_E = 0
	I_{CEO}	—	—	1	mA	V_{CE} = 12 V, R_{BE} = ∞
Emitter cutoff current	I_{EBO}	—	—	10	µA	V_{EB} = 2 V, I_C = 0
DC current transfer ratio	h_{FE}	50	120	250		V_{CE} = 4 V, I_C = 20 mA
Output capacitance	Cob	—	0.8	1.4	pF	V_{CB} = 5 V, I_E = 0, f = 1 MHz
Gain bandwidth product	f_T	4.0	5.8	—	GHz	V_{CE} = 4 V, I_C = 20 mA
Power gain	PG	9.5	13.0	—	dB	V_{CE} = 4 V, I_C = 20 mA, f = 900 MHz
Noise figure	NF	—	1.6	3.0	dB	V_{CE} = 4 V, I_C = 5 mA, f = 900 MHz

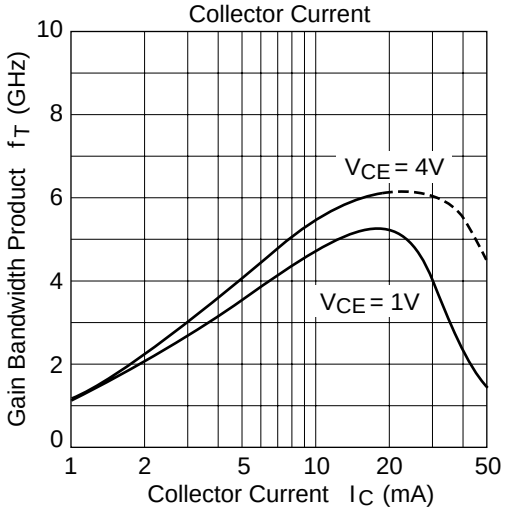
Maximum Collector Power Dissipation Curve



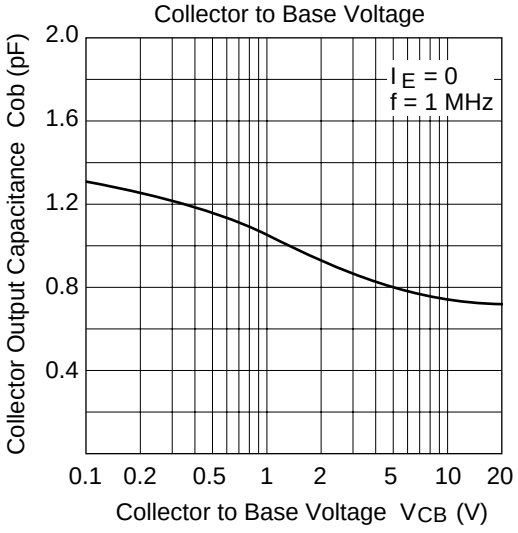
DC Current Transfer Ratio vs. Collector Current



Gain Bandwidth Product vs. Collector Current

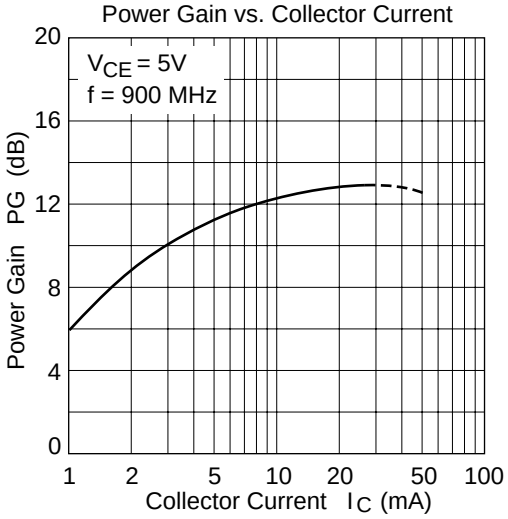


Collector Output Capacitance vs. Collector to Base Voltage

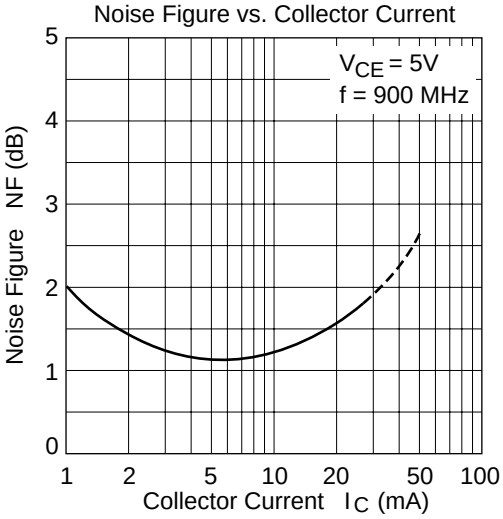


2SC5218

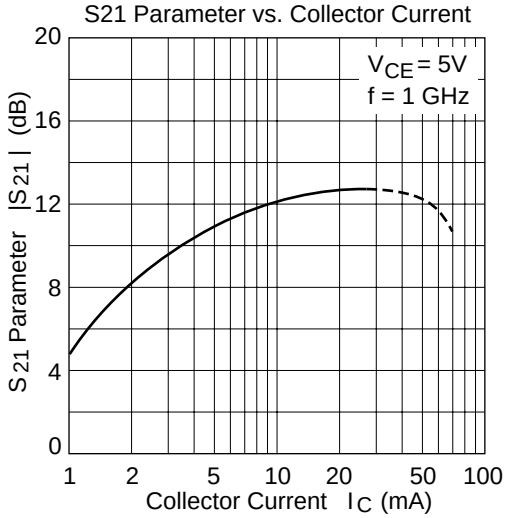
Power Gain vs. Collector Current



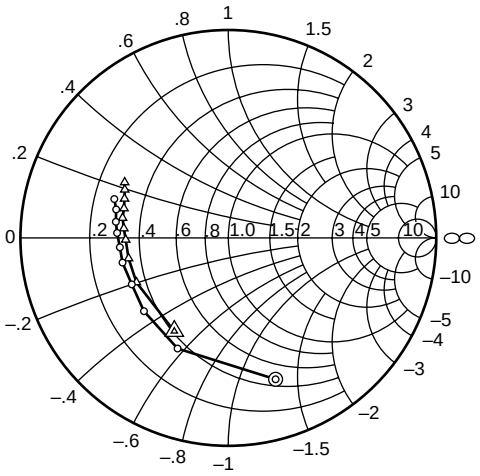
Noise Figure vs. Collector Current



S21 Parameter vs. Collector Current

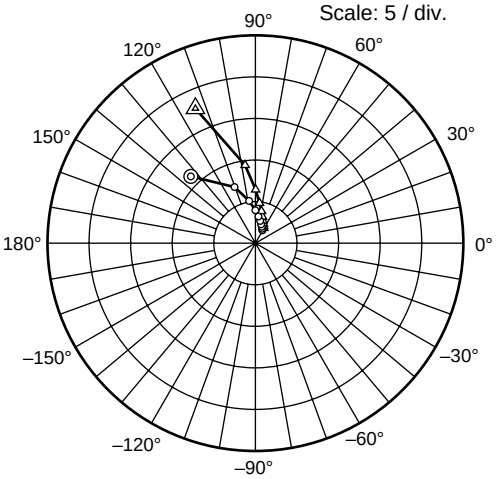


S11 Parameter vs. Frequency



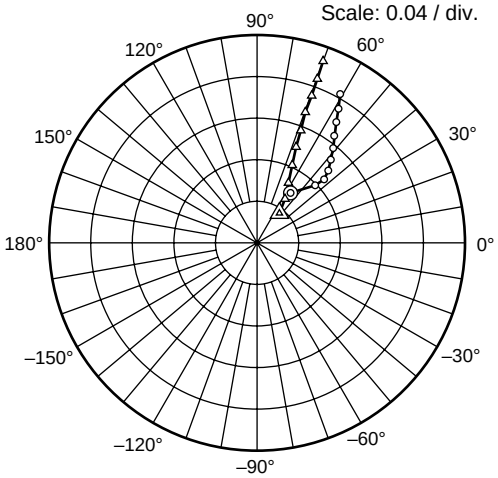
Condition: V_{CE} = 4 V , Zo = 50 Ω
200 to 2000 MHz (200 MHz step)
(I_C = 5 mA)
(I_C = 20 mA)

S21 Parameter vs. Frequency



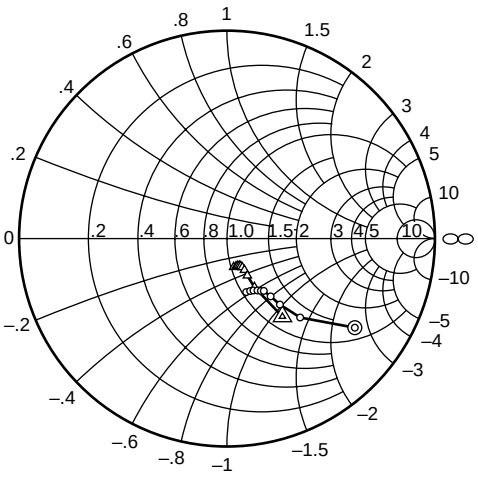
Condition: V_{CE} = 4 V , Zo = 50 Ω
200 to 2000 MHz (200 MHz step)
(I_C = 5 mA)
(I_C = 20 mA)

S12 Parameter vs. Frequency



Condition: V_{CE} = 4 V , Zo = 50 Ω
200 to 2000 MHz (200 MHz step)
(I_C = 5 mA)
(I_C = 20 mA)

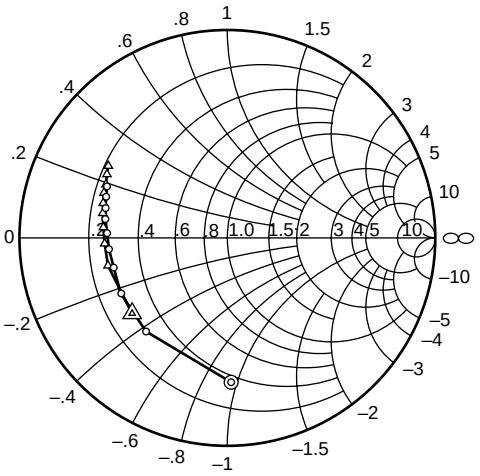
S22 Parameter vs. Frequency



Condition: V_{CE} = 4 V , Zo = 50 Ω
200 to 2000 MHz (200 MHz step)
(I_C = 5 mA)
(I_C = 20 mA)

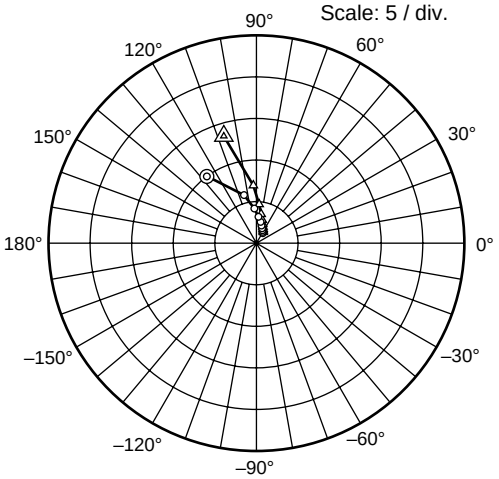
2SC5141

S11 Parameter vs. Frequency



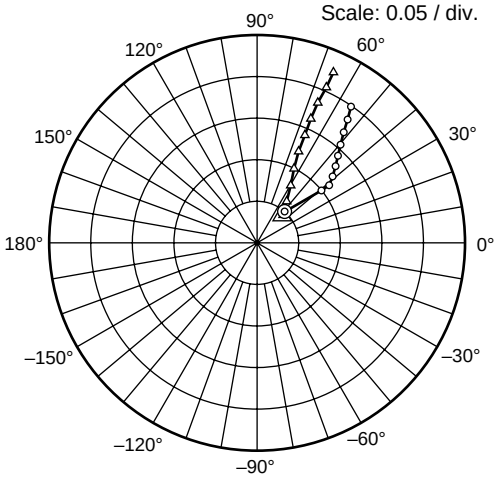
Condition: V_{CE} = 1 V , Zo = 50 Ω
200 to 2000 MHz (200 MHz step)
(I_C = 5 mA)
(I_C = 20 mA)

S21 Parameter vs. Frequency



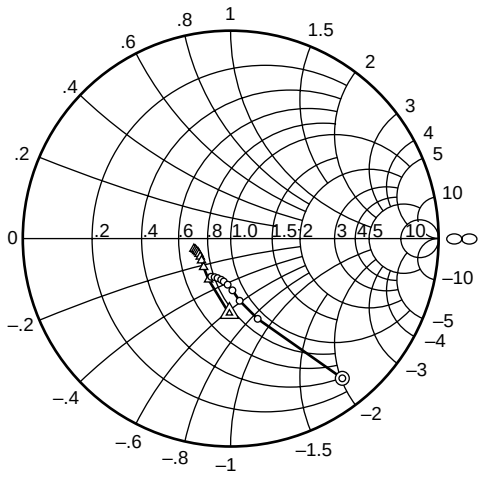
Condition: V_{CE} = 1 V , Zo = 50 Ω
200 to 2000 MHz (200 MHz step)
(I_C = 5 mA)
(I_C = 20 mA)

S12 Parameter vs. Frequency



Condition: V_{CE} = 1 V , Zo = 50 Ω
200 to 2000 MHz (200 MHz step)
(I_C = 5 mA)
(I_C = 20 mA)

S22 Parameter vs. Frequency

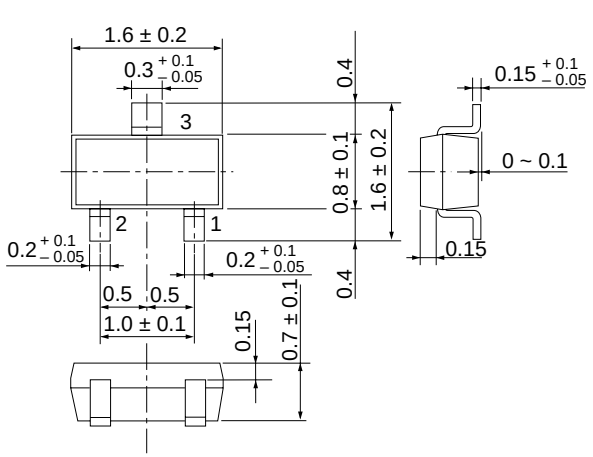


Condition: V_{CE} = 1 V , Zo = 50 Ω
200 to 2000 MHz (200 MHz step)
(I_C = 5 mA)
(I_C = 20 mA)

2SC5141

Package Dimensions

Unit : mm



1. Emitter
2. Base
3. Collector

Hitachi Code	SMPAK
EIAJ	—
JEDEC	—